

SOT-89 Plastic-Encapsulate Transistors

Features

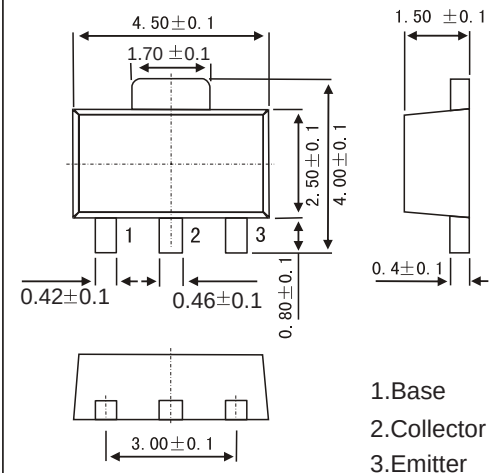
- Collector Current Capability $I_C=-0.2A$
- Collector Emitter Voltage $V_{CEO}=-40V$
- Compliment to PXT3904
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any

SOT-89

Unit:mm



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-40	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-0.2	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

PACKAGE INFORMATION

Device	Package	Shipping
PXT3906 (KXT3906)	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-40			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -30 V, I_E = 0$			-50	nA
Collector- emitter cut-off current	I_{CEX}	$V_{CE} = -30 V, V_{BE(off)} = -3V$			-50	
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 mA, I_B = -1mA$ $I_C = -50 mA, I_B = -5mA$			-0.25 -0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 mA, I_B = -1mA$ $I_C = -50 mA, I_B = -5mA$	-0.65		-0.85 -0.95	
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -0.1mA$ $V_{CE} = -1V, I_C = -1mA$ $V_{CE} = -1V, I_C = -10mA$ $V_{CE} = -1V, I_C = -50mA$ $V_{CE} = -1V, I_C = -100mA$	60 80 100 60 30		300	
Noise figure	NF	$V_{CE} = -5V, I_C = -0.1mA, f = 10Hz-15.7kHz, R_s = 1K\Omega$			4	dB
Delay time	t_d	$I_C = -10mA, I_{B1} = I_{B2} = -1mA$			35	ns
Rise time	t_r				35	
Storage time	t_s				225	
Fall time	t_f				75	
Collector output capacitance	C_{ob}	$V_{CB} = -5V, I_E = 0, f = 1MHz$			4.5	pF
Emitter capacitance	C_e	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$			10	
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	250			MHz

■ Marking

Marking	2A
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